

Description



The A125N50X4 is high performance Aluminum Nitride (AlN) chip termination intended as an alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators and for use in power combiners. The termination is also RoHS compliant!

General Specifications

Resistive Element	Thick film
Substrate	AlN Ceramic
Terminal Finish	Matte Tin over Nickel Barrier
Operating Temperature	-55 to +150°C (see de rating chart)

Tolerance is ± 0.010 ", unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. **All dimensions in inches.**

Electrical Specifications

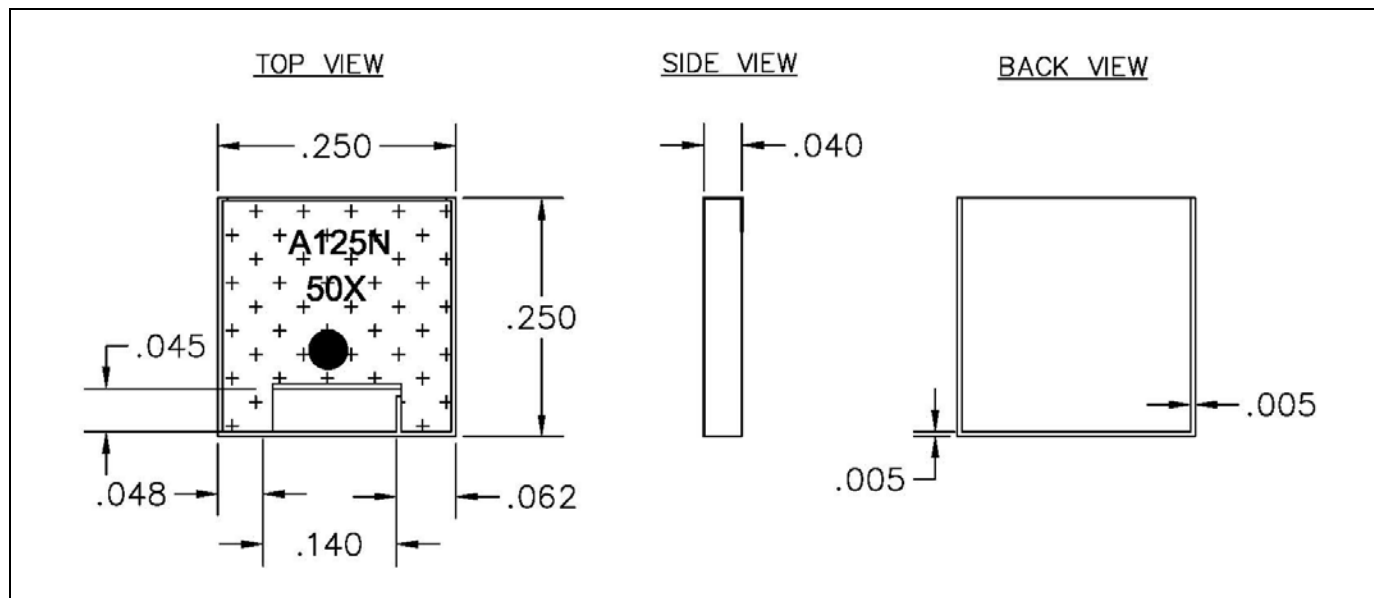
Resistance Value:	50 Ohms, $\pm 2\%$
Power:	125 Watts
Frequency Range:	DC – 4.0 GHz
Return Loss	> 26 dB to 2.7 GHz > 20 dB to 4.0 GHz

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.**

Features:

- RoHS Compliant
- 125 Watts
- DC – 4.0 GHz
- AlN Ceramic
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested
- Small Size

Outline Drawing

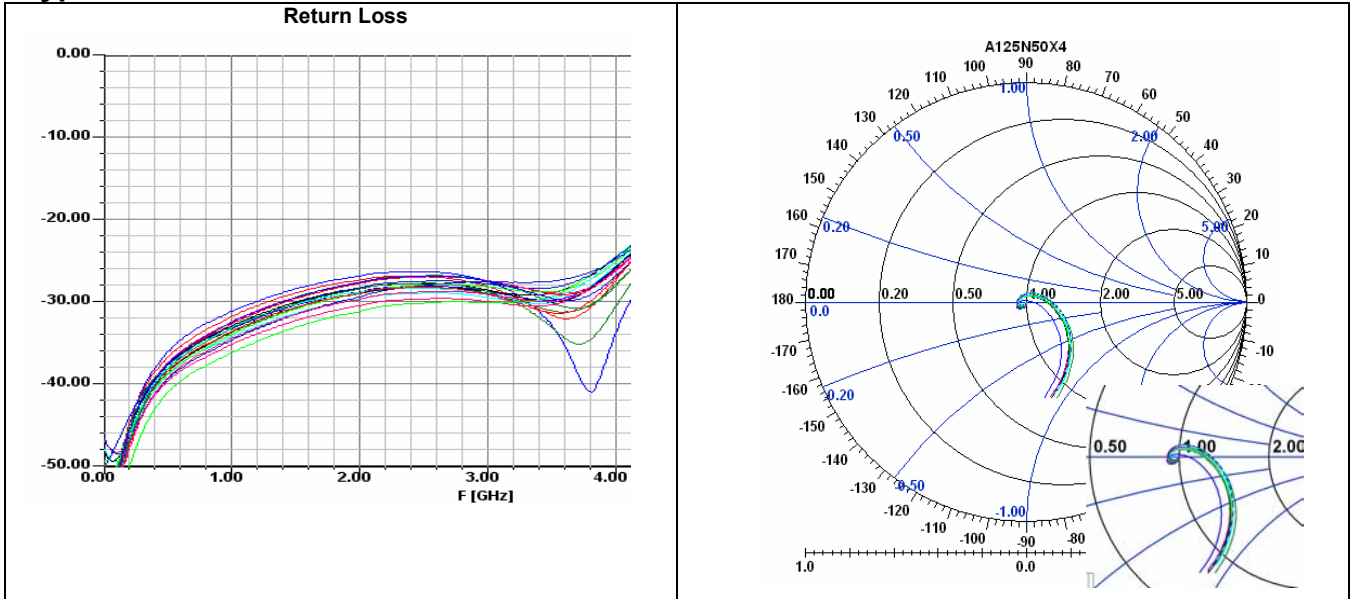


A125N50X4 (097) rev.D pg.1 of 2

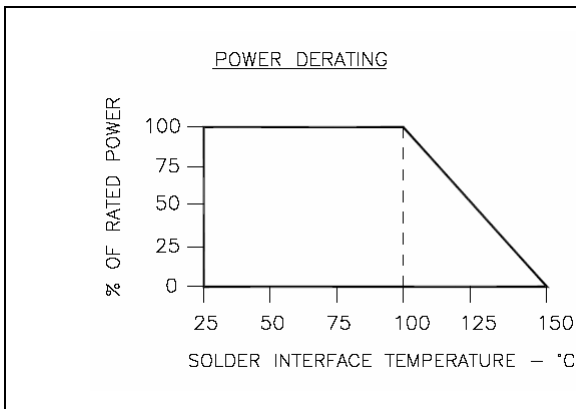




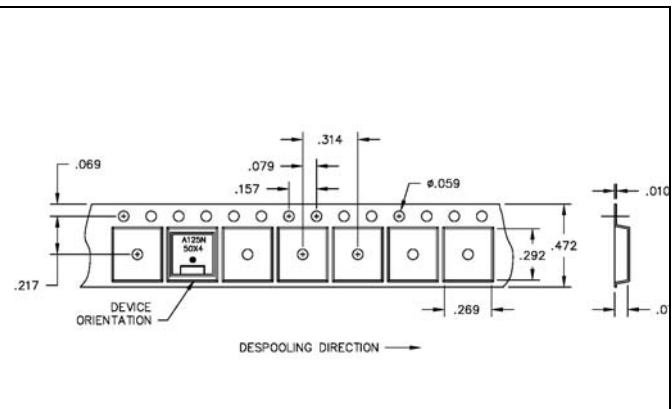
Typical Performance:



Power De-rating:



Tape & Reel:



Mounting Footprint and Procedure:

